

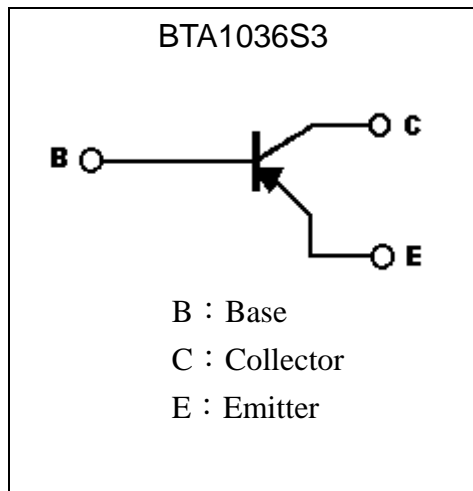
General Purpose PNP Epitaxial Planar Transistor

BTA1036S3

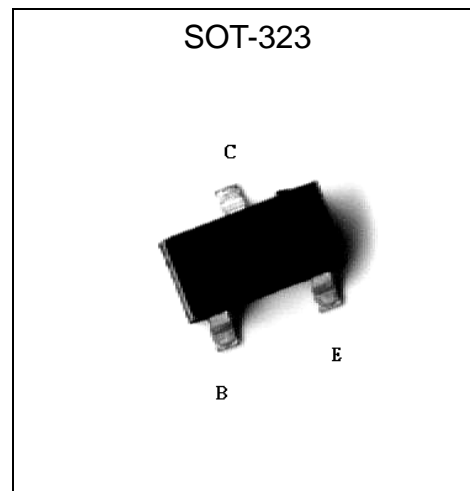
Description

- The BTA1036S3 is designed for general purpose amplifier applications. It is housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.
- Low $V_{CE(sat)}$
- High switching speed.
- Complementary to BTC2411S3
- Pb-free lead plating and halogen-free package

Symbol

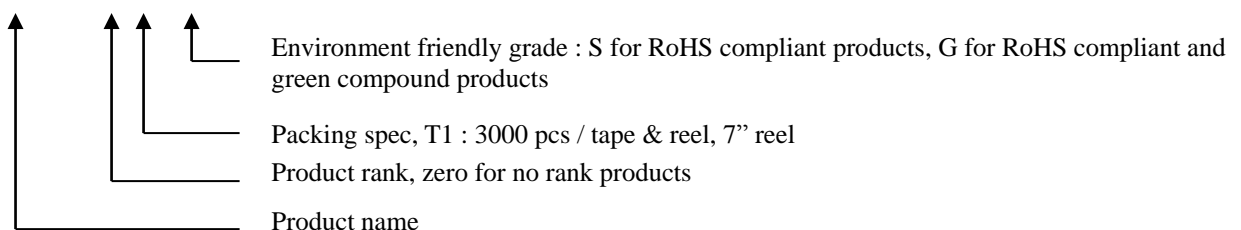


Outline



Ordering Information

Device	Package	Shipping
BTA1036S3-0-T1-G	SOT-323 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA
Power Dissipation	P _D	150 (Note 1)	mW
Operating Junction Temperature Range	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Note 1:When mounted on a FR-5 board with area measuring 1.0x0.75x0.062 in.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-ambient, max	R _{th,j-a}	833	°C/W

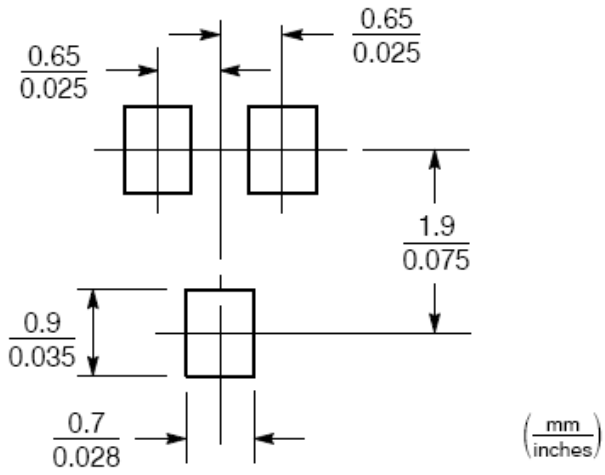
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-60	-	-	V	I _C =-10μA
*BV _{CEO}	-60	-	-	V	I _C =-10mA
BV _{EBO}	-5	-	-	V	I _E =-10μA
I _{CB0}	-	-	-10	nA	V _{CB} =-50V
I _{CEX}	-	-	-50	nA	V _{CE} =-30V, V _{BE(OFF)} =-0.5V
*V _{CE(sat)}	-	-0.2	-0.4	V	I _C =-150mA, I _B =-15mA
*V _{CE(sat)}	-	-0.5	-1.6	V	I _C =-500mA, I _B =-50mA
*V _{BE(sat)}	-	-	-1.3	V	I _C =-150mA, I _B =-15mA
*V _{BE(sat)}	-	-	-2.6	V	I _C =-500mA, I _B =-50mA
*h _{FE}	75	-	-	-	V _{CE} =-10V, I _C =-100μA
*h _{FE}	100	-	-	-	V _{CE} =-10V, I _C =-1mA
*h _{FE}	100	-	-	-	V _{CE} =-10V, I _C =-10mA
*h _{FE}	100	-	300	-	V _{CE} =-10V, I _C =-150mA
*h _{FE}	50	-	-	-	V _{CE} =-10V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-20V, I _C =-50mA, f=100MHz
C _{ob}	-	-	8	pF	V _{CB} =-10V, I _E =0A, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%



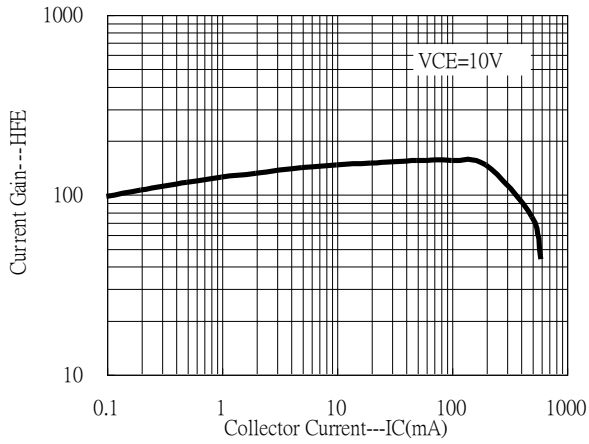
Recommended Soldering Footprint



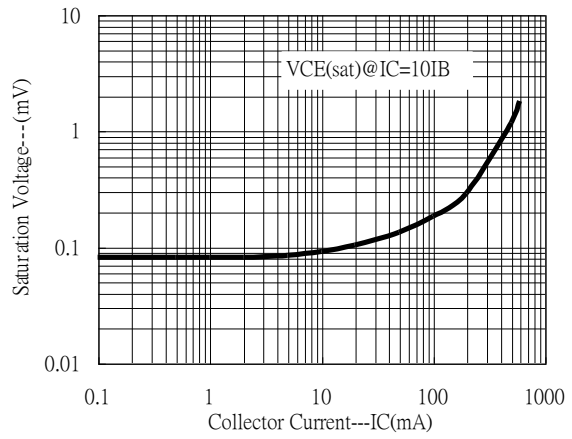


Typical Characteristics

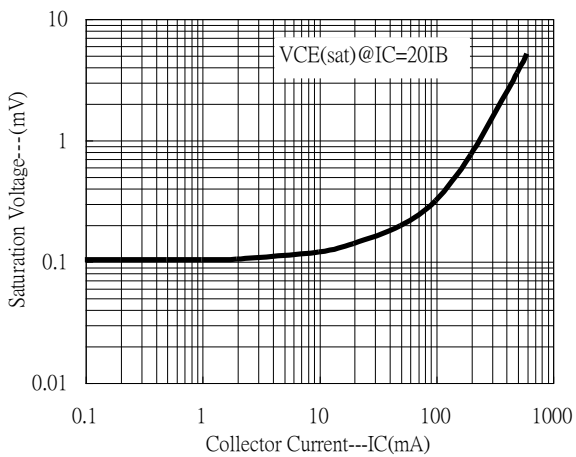
Current Gain vs Collector Current



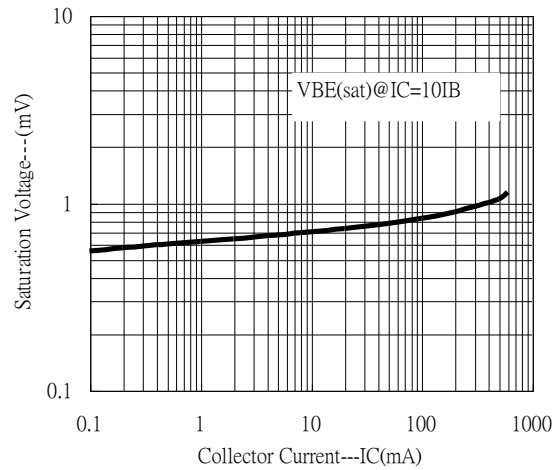
Saturation Voltage vs Collector Current



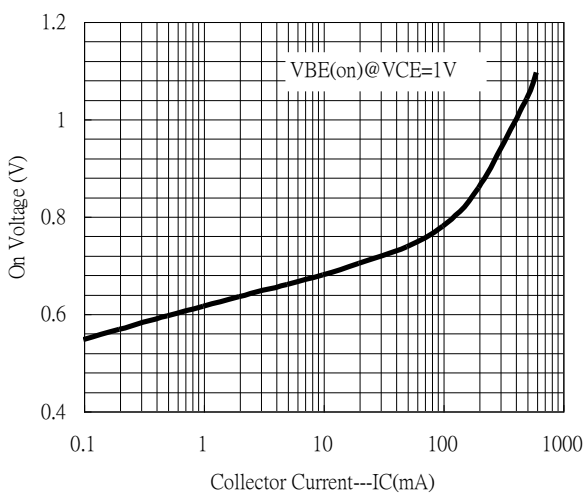
Saturation Voltage vs Collector Current



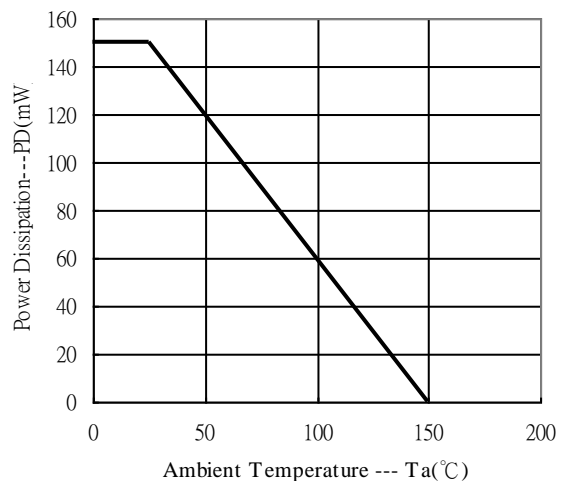
Saturation Voltage vs Collector Current



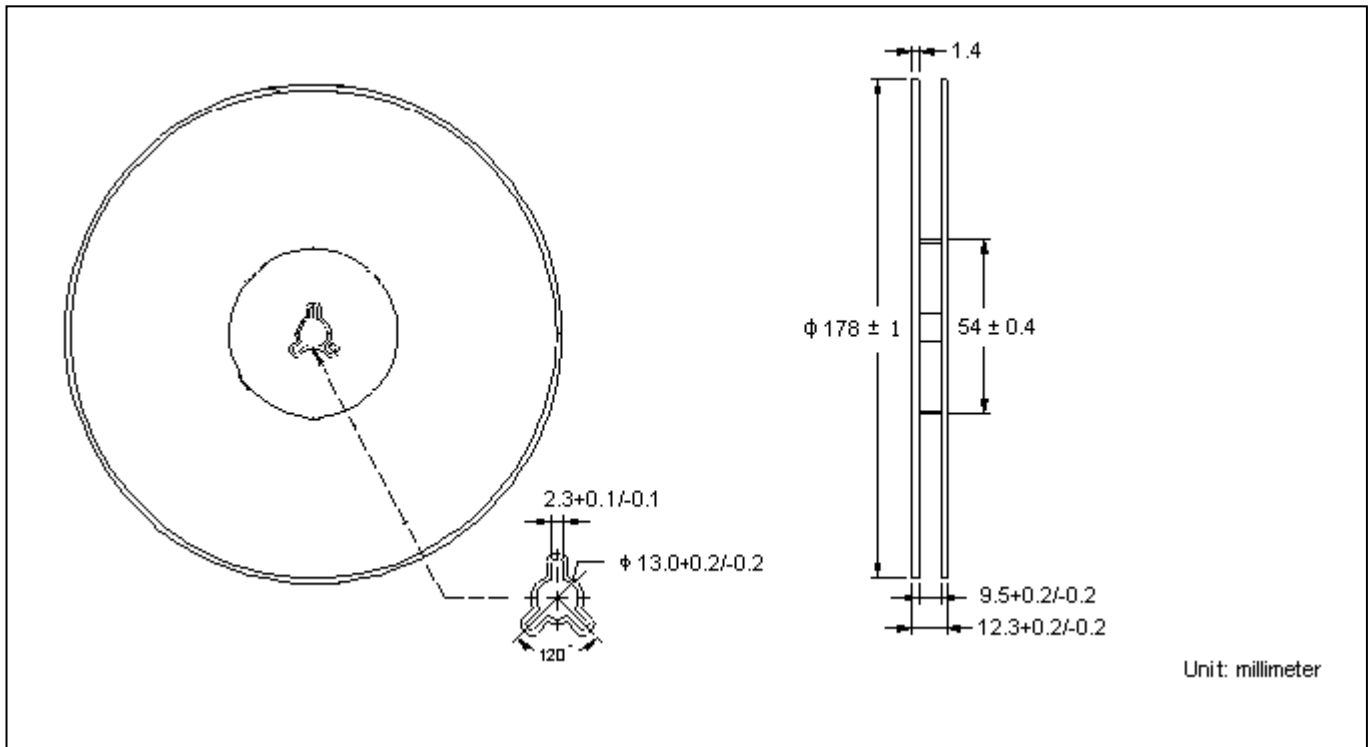
On Voltage vs Collector Current



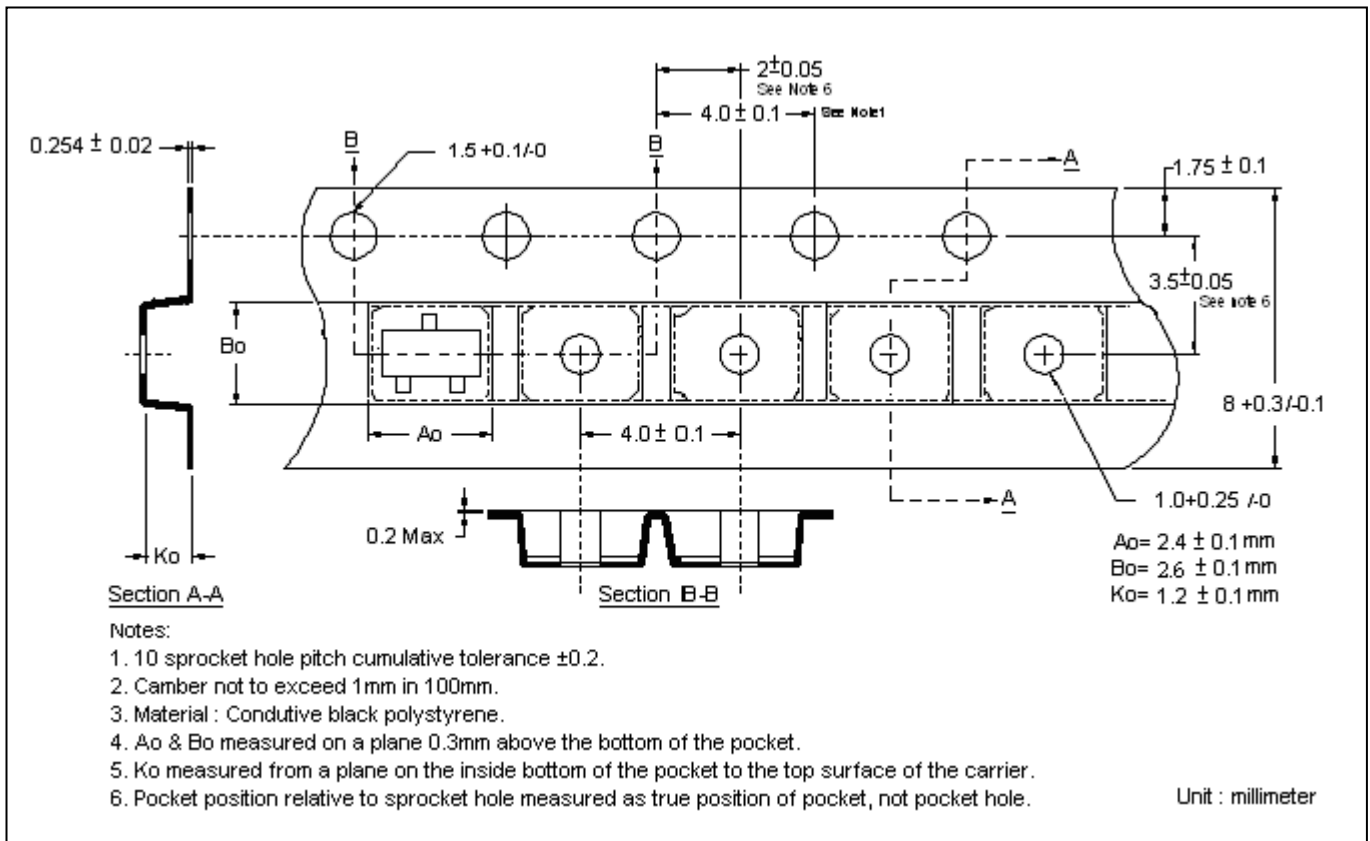
Power Derating Curve



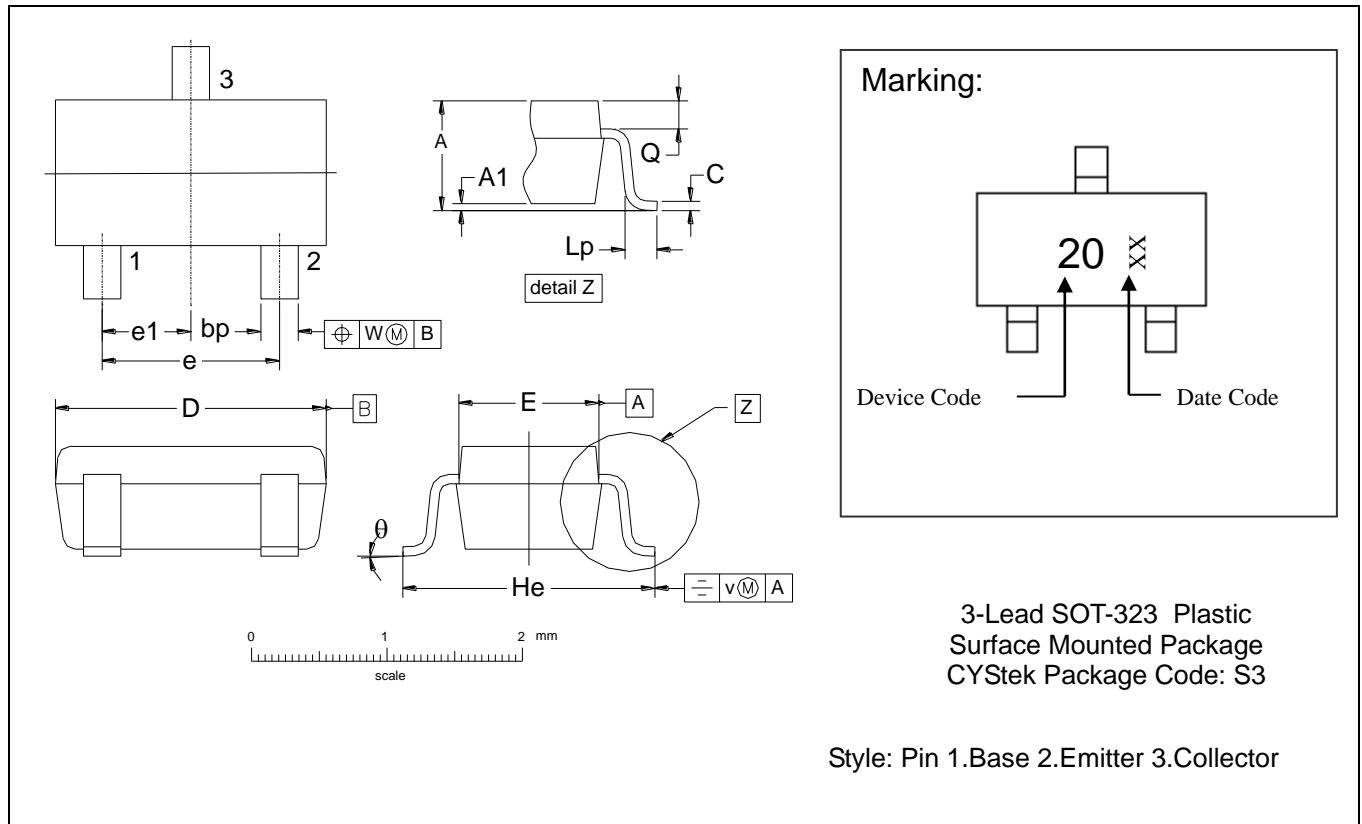
Reel Dimension



Carrier Tape Dimension



SOT-323 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0315	0.0433	0.80	1.10	e1	0.0256*		0.65*	
A1	0.0000	0.0039	0.00	0.10	He	0.0846	0.0965	2.15	2.45
bp	0.0078	0.0157	0.20	0.40	Lp	0.0105	0.0181	0.26	0.46
C	0.0031	0.0059	0.08	0.15	Q	0.0051	0.0091	0.13	0.23
D	0.0709	0.0866	1.80	2.20	v	0.0079	-	0.2	-
E	0.0453	0.0531	1.15	1.35	w	0.0079	-	0.2	-
e	0.0472	0.0551	1.20	1.40	θ	0°	8°	0°	8°

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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